

U.S. UTILITY Patent Application

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Γ	10008204	12/05/2001	438		2812	NO -	12-2-Le				
	*APPLICANTS: Chern Geeng-Chuan; Levi Amitay; Lee Dana;										
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	35 USC 119 condit	ions met		0100007 001000	;						
	Verified and Acknowledged Examiners's initials 2102397-991220										
	TITLE: Method of forming different oxide thickness for high voltage transistor and memory cell tunnel dielectric										
	L		:- -			U.S.DEPT. OF COMM./PAT.	8 TM-FTO-436L(Rev. 12-94),				
OTICE OF ALLOWANCE MAILED CLAIMS ALLOWED											
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			Assistant Examiner			O.G					
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NOTICE OF ALLOWANCE MAILED			CLAIMS ALLOWED					
		Assistant Examiner	Total Claims		Print Claim for O.G			
ISS	UE FEE		DRAWING					
Amount Due	Date Paid		Sheets Drwg.	Figs.Drwg.	Print Fig.			
	<u> </u>	Primary Examiner		<u> </u>				
TER	RMINAL	PREPARED FOR ISSUE	Application Examiner					
· · · · · · · · · · · · · · · · · · ·	DISCLAMER	WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.						
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